

GaAs PIN PHOTODIODES

PD-8150 Series

PIN Photodiode with Mini-Size TO Package

FEATURES

- 2 High Responsivity for 850 nm
- 2 Low Dark Current
- 2 Quick Pulse Response
- 2 **2.4 mm Mini-Size Package**
- 2 Active Diameter 100 μ m

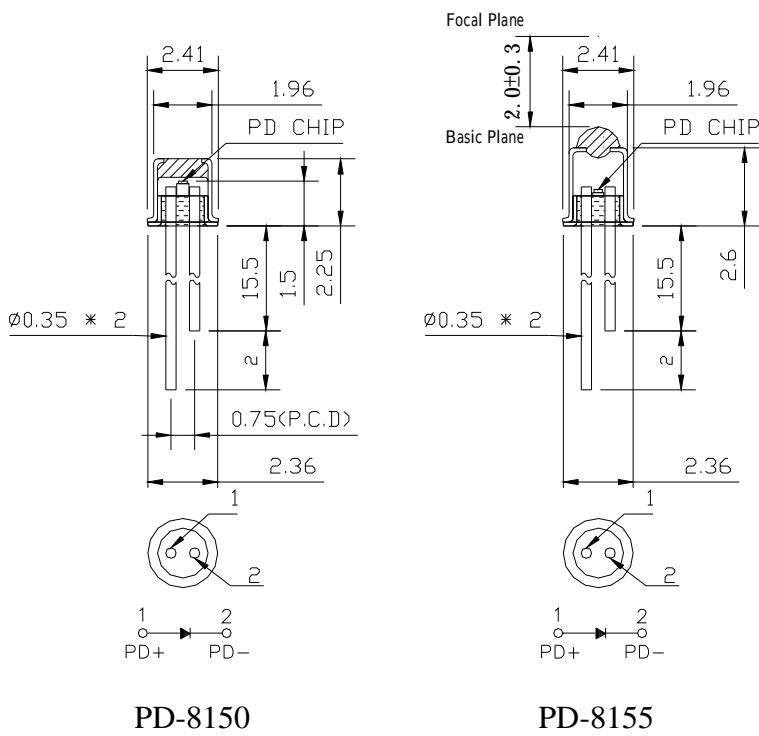
DESCRIPTION

PD-8150 series InGaAs Photodiode are suited to receive the light at the wavelength range from 600 nm to 1000 nm. With high reliability, PD-8150 series are the best choice for datacom application.

PD-8160-100 ELECTRICAL AND OPTICAL CHARACTERISTICS (T_C=25°C)						
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
	Active Area			100		μ m
	Detection Range		600		1000	nm
R	Responsivity	V _R =5V, λ =850nm	0.45	0.5	-	A/W
I _{dark}	Dark Current	V _R =5V			0.5	nA
C	Capacitance	V _R =5V			0.7	pF
T _r /T _f	Rise/Fall Time	V _R =5V, 10~90%			0.3	ns
BW	Bandwidth	V _R =5V	2			GHz

ABSOLUTE MAXIMUM RATINGS (T_C=25 °C)			
Symbol	Parameter	Ratings	Unit
P _o	Input Optical Power	10	mW
V _{RD}	Reverse Voltage	20	V
I _{FD}	Forward Current	10	mA
T _{opr}	Operating Temperature	-40~+85	°C
T _{stg}	Storage Temperature	-40~+85	°C

MECHANICAL DIMENSION (mm) and PIN ASSIGNMENT



ORDER INFORMATION

Part No.: P D - 8 1 5 -

Code	Cap
0	Flat Window
5	Ball lens

Code	Chip Diameter
100	100 μm